MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

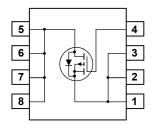
Broduct data sheet







SOP-8



1 Source 5 Drain 2 Source 6 Drain 3 Source 7 Drain 8 Drain 4 Gate

Features

- VDS (V) =-30V
- ID =-5.3 A (VGS =-10V)
- RDS(ON) < 50m Ω (VGS =-10V)
- RDS(ON) < 80m Ω (VGS =-4.5V)
- Fast switching speed

Absolute Maximum Ratings Ta = 25° C

Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		VDS	-30	V	
Gate-Source Voltage		Vgs	±20	V	
Continuous Drain Current		ΙD	-5.3	Α	
Pulsed Drain Current			-20		
	(Note.1) (Note.2) (Note.3)	Po	2.5		
			1.2	W	
			1		
Thermal Resistance.Junction- to-Ambient		RthJA	50	°C/W	
Thermal Resistance.Junction- to-Case		RthJC	25		
Junction Temperature		TJ	150	°C	
Junction Storage Temperature Range		Tstg	-55 to 150		

Note.1: 50°C/W when mounted on a 1in² pad of 2 oz copper

Note.2: 105°C/W when mounted on a .04 in² pad of 2 oz copper

Note.3: 125°C/W when mounted on a minimum pad.



■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	VDSS	ID=-250 μ A, VGS=0V	-30			V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =-24V, V _{GS} =0V			-1	μА
Gate-Body leakage current	Igss	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	VGS(th)	VDS=VGS ID=-250 μ A	-1		-3	V
Static Drain-Source On-Resistance	Rds(on)	Vgs=-10V, Ip=-5.3A (Note.1)			50	
		Vgs=-10V, Ip=-5.3A ,TJ=125°C (Note.1)			79	mΩ
		Vgs=-4.5V, Ip=-4.2A (Note.1)			80	
On state drain current	ID(ON)	VGS=-10V, VDS=-5V (Note.1)	-20			Α
Forward Transconductance	grs	VDS=-15V, ID=-5.3A (Note.1)		12		S
Input Capacitance	Ciss	Vgs=0V, Vds=-15V, f=1MHz		690		pF
Output Capacitance	Coss			306		
Reverse Transfer Capacitance	Crss			77		
Total Gate Charge	Qg	Vgs=-15V, Vds=-10V, ld=-5.3A		14	23	
Gate Source Charge	Qgs			2.4		nC
Gate Drain Charge	Qgd			4.8		
Turn-On DelayTime	td(on)			7	14	
Turn-On Rise Time	tr	Vgs=-10V, Vds=-15V, ld=-1A,Rg=6 Ω		10	18	ns
Turn-Off DelayTime	td(off)			19	34	
Turn-Off Fall Time	tf			11	20	
Maximum Body-Diode Continuous Current	Is				-5.3	Α
Diode Forward Voltage	Vsd	Is=-5.3A,VGs=0V (Note.1)			-1.2	V

Note.1: Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%



■ Typical Characterisitics

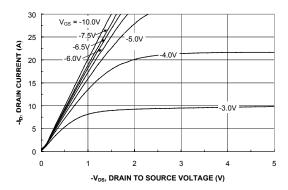


Figure 1. On-Region Characteristics.

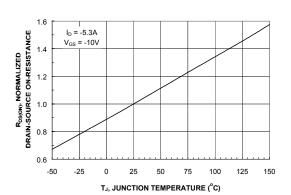


Figure 3. On-Resistance Variation with Temperature.

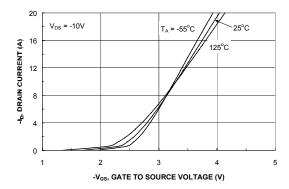


Figure 5. Transfer Characteristics.

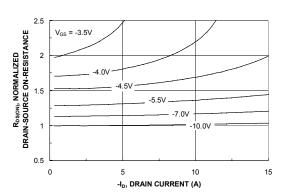


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

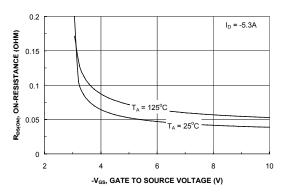


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

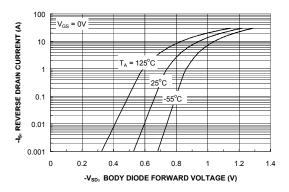
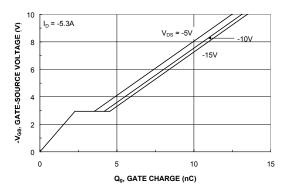


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.



■ Typical Characterisitics



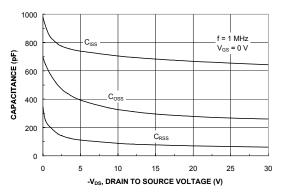
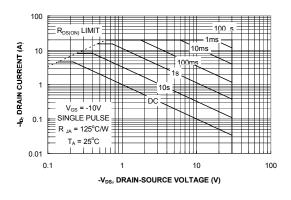


Figure 7. Gate Charge Characteristics.





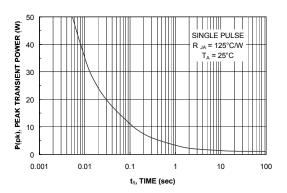


Figure 9. Maximum Safe Operating Area.

Figure 10. Single Pulse Maximum Power Dissipation.

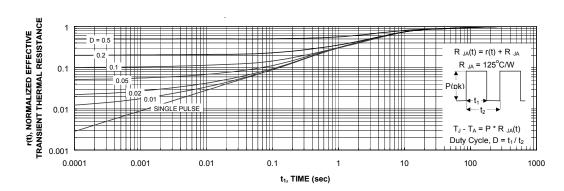
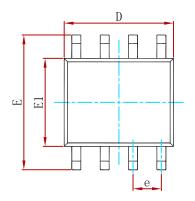


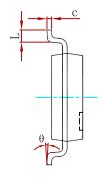
Figure 11. Transient Thermal Response Curve.

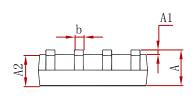
Thermal characterization performed using the conditions described in Note 1c. Transient thermal response will change depending on the circuit board design.



PACKAGE MECHANICAL DATA

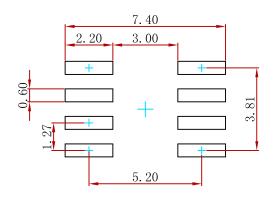






Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
3y 111001	Min	Max	Min	Max	
A	1.350	1.750	0.053	0.069	
A1	0.100	0.250	0.004	0.010	
A2	1.350	1.550	0.053	0.061	
b	0.330	0.510	0.013	0.020	
С	0.170	0.250	0.007	0.010	
D	4.800	5. 000	0.189	0. 197	
e	1. 270	(BSC)	0.050	(BSC)	
Е	5.800	6. 200	0. 228	0. 244	
E1	3.800	4.000	0.150	0. 157	
L	0.400	1.270	0.016	0.050	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1.Controlling dimension:in millimeters.
 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY			
MS9435	SOP-8	3000			



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